

**NPN Bipolar RF power transistor**

**MRF410**

**Description:**

MRF410 is designed primarily for HF, VHF, UHF, 800MHz, and Microwave applications in military and commercial land mobile, avionics, and marine transmitters.

**Features:**

1.5-30MHz, HF/SSB Transistors. Designed for broadband operation, these devices feature specified intermodulation distortion at rated power output. Applications include mobile, marine, fixed station, and amateur HF/SSB equipment, operating from 12.5, 13.6, 28 or 50 volt supplies.

Pout: 10PEP/CW, Pin: 0.5Watts, Min Gpe: 13dB, Vcc: 28V, Package: 211-07 or SOT120

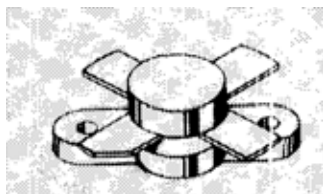
**Maximum Ratings at TU = 25**

Symbol	Test Conditions	Characteristics		Units
BVCEs	IC=10 mA	Max.	65	V
BVCEO	IC=30 mA	Max.	35	V
BVEBO	IE =5 mA	Max.	4	V
IC		Max.	1.5	A
Ptot		Max.	40	W
TSTG		Min.	-65	
		Max.	150	
TjM		Max.	175	

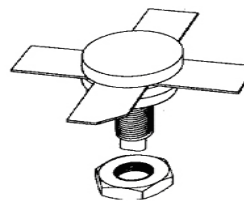
**Characteristics at TU = 25 ( VCC =28 V f=30 MHz )**

Symbol	Test Conditions	Characteristics		Units
Pout		Typ.	10PEP	W
GP		Typ.	20	dB
$\eta$		Typ.	45	%
hFE	IC = 0.5A VCE =10V	Typ.	50	
VCEsat	IC = 2A IB =0.4 A	Max.	1.2	V
ICES	VCE =36V	Max.	5	mA
CCBO	VCB =28V	Typ.	80	pF
d3		Max.	< -30	dB

**Drawings:**



**CASE211-07**



**SOT120**